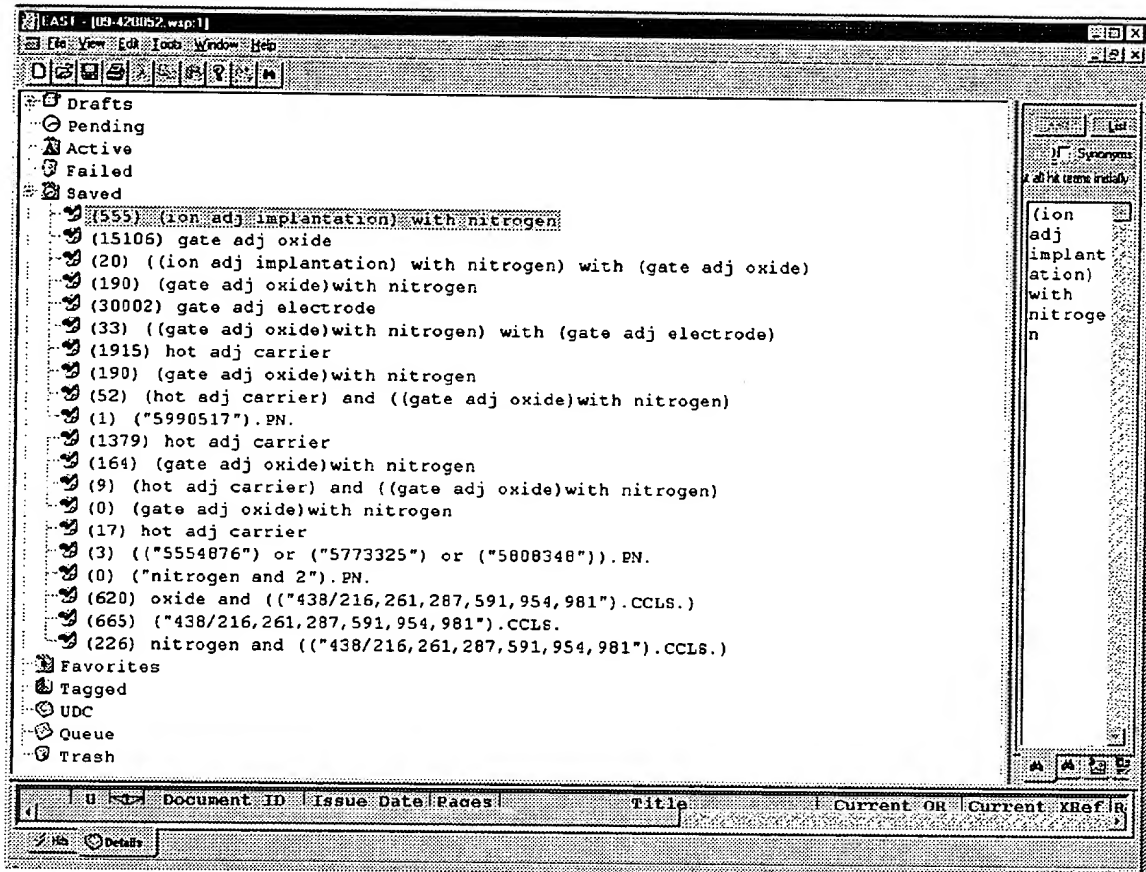


Type	Hits	Search Text	DBs	Time Stamp
1 BRS	225	ortiz xa.	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/02/24 11:21
2 BRS	189	Edgar\$3 xa.	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/02/24 11:21
3 BRS	89	ortiz xa. and Edgar\$3 xa.	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/02/24 11:22
4 BRS	40	gate adj oxide and (ortiz xa. and Edgar\$3 xa.)	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/02/24 11:23
5 BRS	15	(gate adj oxide and (ortiz xa. and Edgar\$3 xa.) and (gate adj oxide same (nitrogen or "N" or "N sub 2" or "NO" or "NO sub 2"))	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/02/24 11:30
6 BRS	7585	(gate adj oxide with (nitrogen or "N" or "N sub 2" or "NO" or "NO sub 2"))	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/02/24 11:34
7 BRS	1783	(gate adj oxide) with (nitrogen or "N sub 2" or "NO" or "NO sub 2"))	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/02/24 11:36
8 BRS	1296	(gate adj oxide) with ("NO" or "NO sub 2")	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/02/24 11:38
9 BRS	17303676	@ad<=19970827	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/02/24 11:40
10 BRS	598234	@rtad<=19970827	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/02/24 11:40
11 BRS	5585	((gate adj oxide with (nitrogen or "N" or "N sub 2" or "NO" or "NO sub 2")) and @ad<=19970827	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/02/24 11:44
12 BRS	1295	((gate adj oxide with (nitrogen or "N" or "N sub 2" or "NO" or "NO sub 2")) and @rtad<=19970827	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/02/24 11:43
13 BRS	5849	((gate adj oxide with (nitrogen or "N" or "N sub 2" or "NO" or "NO sub 2")) and @ad<=19970827 ((gate adj oxide with (nitrogen or "N" or "N sub 2" or "NO" or "NO sub 2")) and @rtad<=19970827	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/02/24 11:43
14 BRS	773	((gate adj oxide) with ("NO" or "NO sub 2")) and @ad<=19970827	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/02/24 11:44
15 BRS	271	((gate adj oxide) with ("NO" or "NO sub 2")) and @rtad<=19970827	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/02/24 11:44
16 BRS	835	((gate adj oxide) with ("NO" or "NO sub 2")) and @ad<=19970827 ((gate adj oxide) with ("NO" or "NO sub 2")) and @rtad<=19970827	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/02/24 11:45
17 BRS	0	5990517 URPN	USPAT	2002/02/24 11:59
18 BRS	3	("5554876"   "5773325"   "5808348"), PN.	USPAT	2002/02/24 11:59
19 IS&R	2	("5990517"), PN.	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/02/24 16:07
20 BRS	0	5990517 URPN.	USPAT	2002/02/24 16:08
21 BRS	3	("5554876"   "5773325"   "5808348"), PN.	USPAT	2002/02/24 16:09

2/25/02



The screenshot shows the EAS-1 software interface. At the top is a menu bar with 'File', 'View', 'Edit', 'Tools', 'Window', and 'Help'. Below the menu is a toolbar with various icons. The main window is divided into two panes. The left pane, titled 'Saved', contains a list of documents with their titles and issue dates. The right pane, titled 'Favorites', contains a list of documents with their titles and issue dates. The 'Favorites' list is currently empty. The 'Saved' list contains the following documents:

Document ID	Issue Date	Pages	Title	Current OR	Current XRef
US 5691212 A	19960910	7	MOS device structure and integration method		
JP 04010547 A		5	MANUFACTURE OF SEMICONDUCTOR DEVICE		
JP 04139882 A		5	THIN FILM TRANSISTOR		
US 5554871 A	19960910	51	Semiconductor device having MOS transistor with nitrogen doping	257/336	257/344 257/408
US 5691212 A	19971125	7	MOS device structure and integration method	438/297	438/300 438/303
US 5702988 A	19971230	33	Blending integrated circuit technology	438/238	438/199 438/253
US 5731233 A	19980324	50	Semiconductor device having MOS transistor and method of manufacturing	438/199	438/219 438/231
US 5861335 A	19990119	9	Semiconductor fabrication employing a post-implant anneal within a low	438/308	438/227 438/301
US 5911103 A	19990608	50	Semiconductor device having MOS transistor and method of manufacturing	438/199	438/219 438/231
US 5937300 A	19990810	24	Semiconductor apparatus and fabrication method thereof	438/300	438/303 438/586
US 5960319 A	19990928	49	Fabrication method for a semiconductor device	438/564	438/649 438/651